



ST330S SERIES

PHASE CONTROL THYRISTORS

Stud Version

Features

- Center amplifying gate
- Hermetic metal case with ceramic insulator
- International standard case TO-209AE (TO-118)
- Threaded studs UNF 3/4 - 16UNF2A or ISO M24x1.5
- Compression Bonded Encapsulation for heavy duty operations such as severe thermal cycling

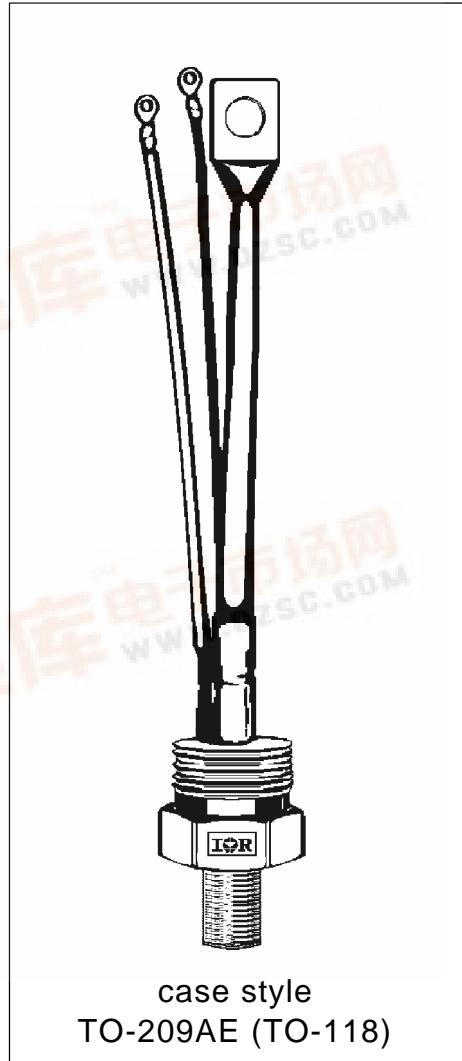
330A

Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	ST330S	Units
$I_{T(AV)}$	330	A
@ T_C	75	°C
$I_{T(RMS)}$	520	A
I_{TSM}	9000	A
@ 50Hz	9000	A
@ 60Hz	9420	A
I^2t	405	KA ² s
@ 50Hz	405	KA ² s
@ 60Hz	370	KA ² s
V_{DRM}/V_{RRM}	400 to 1600	V
t_q	typical	μs
T	- 40 to 125	°C



ST330S Series

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max mA
ST330S	04	400	500	50
	08	800	900	
	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

On-state Conduction

Parameter	ST330S	Units	Conditions
$I_{T(AV)}$ @ Case temperature	330	A	180° conduction, half sine wave
	75	°C	
$I_{T(RMS)}$	520	A	DC @ 62°C case temperature
I_{TSM} Max. peak, one-cycle non-repetitive surge current	9000	A	t = 10ms t = 8.3ms t = 10ms t = 8.3ms
	9420		No voltage reapplied
	7570		100% V_{RRM} reapplied
	7920		reapplied
I^2t Maximum I^2t for fusing	405	KA ² s	t = 10ms t = 8.3ms t = 10ms t = 8.3ms
	370		No voltage reapplied
	287		100% V_{RRM} reapplied
	262		
$I^2\sqrt{t}$	4050	KA ² /s	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.91	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ max.
$V_{T(TO)2}$ High level value of threshold voltage	0.92		$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ max.
r_{t1} Low level value of on-state slope resistance	0.58	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$, $T_J = T_J$ max.
r_{t2} High level value of on-state slope resistance	0.57		$(I > \pi \times I_{T(AV)})$, $T_J = T_J$ max.
V_{TM}	1.51	V	$I_{pk} = 1040A$, $T_J = T_J$ max, $t_p = 10ms$ sine pulse
I_H	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load
I_L	1000		

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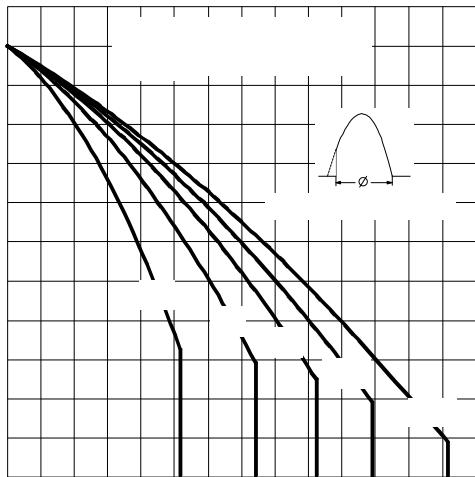


Fig. 1 - Current Ratings Characteristics

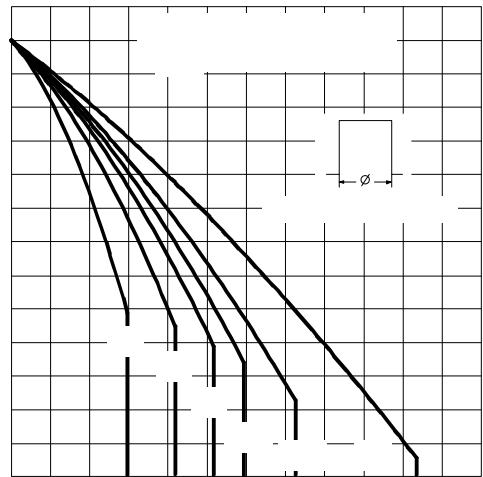


Fig. 2 - Current Ratings Characteristics

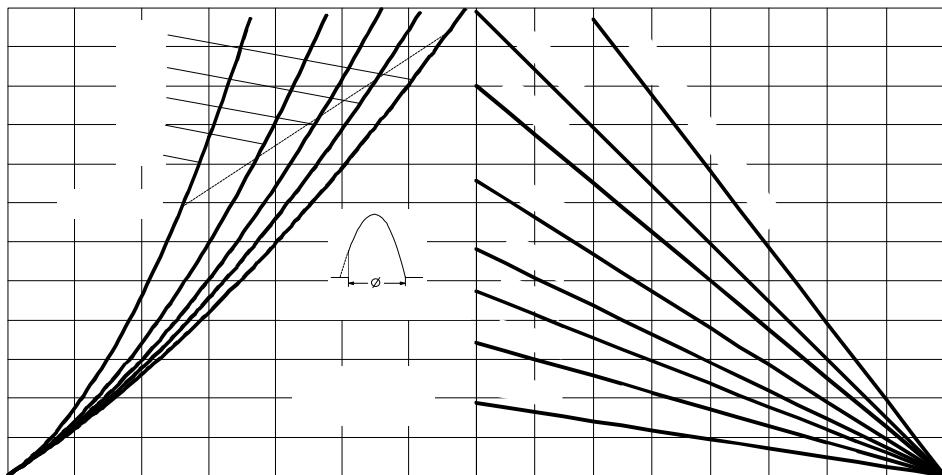
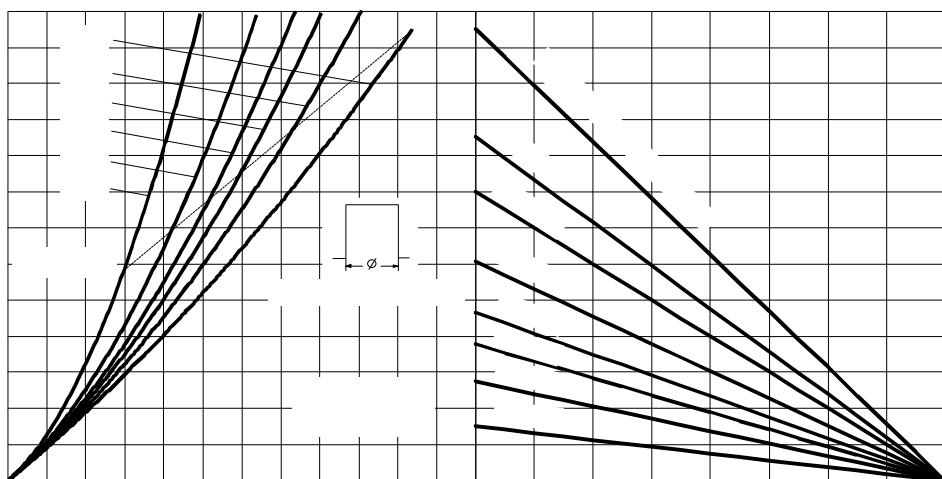


Fig. 3 - On-state Power Loss Characteristics



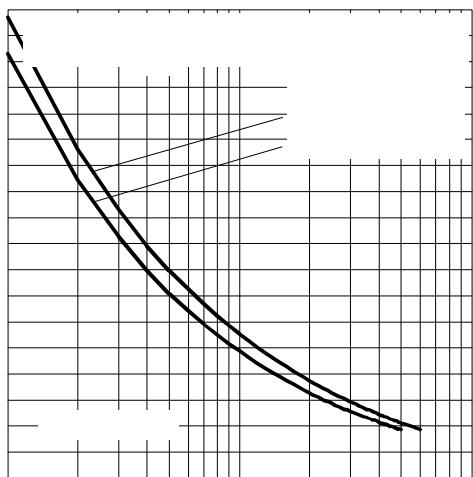


Fig. 5 - Maximum Non-Repetitive Surge Current

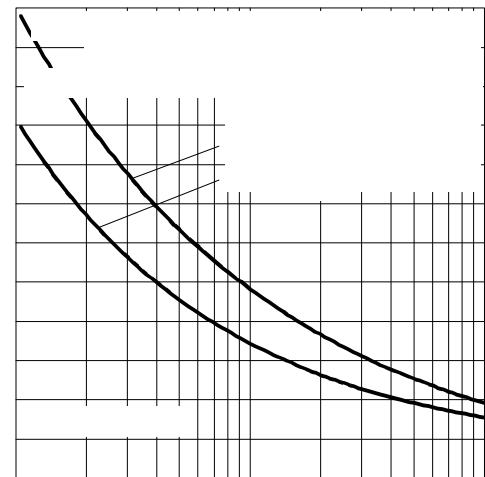


Fig. 6 - Maximum Non-Repetitive Surge Current

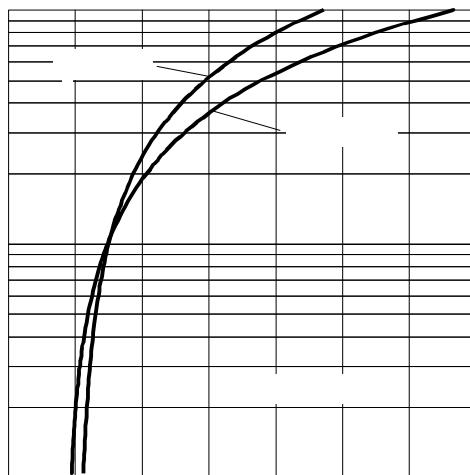
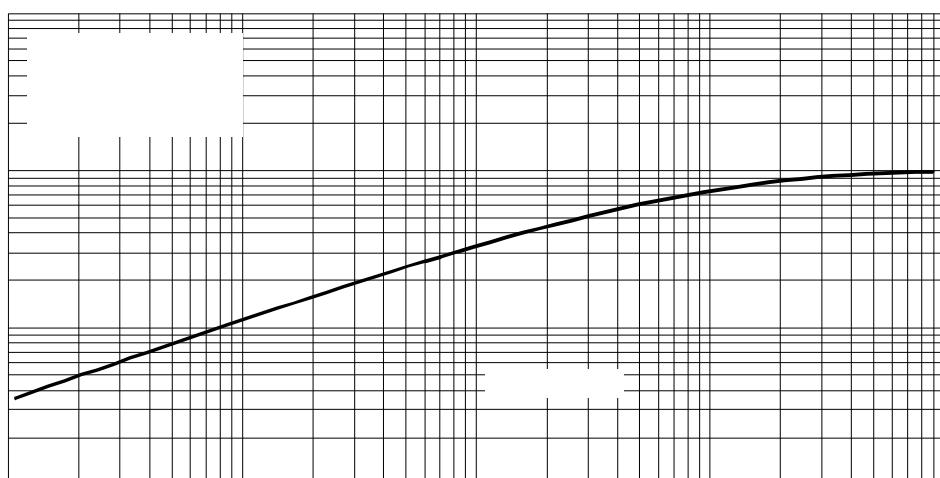


Fig. 7 - On-state Voltage Drop Characteristics



ST330S Series

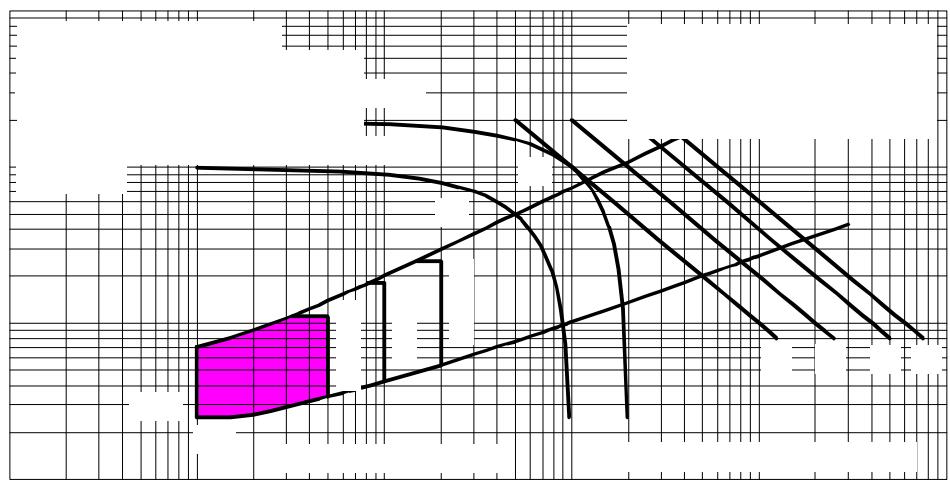


Fig. 9 - Gate Characteristics

Switching

Parameter	ST330S	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_{J\max}$, anode voltage $\leq 80\% V_{DRM}$
t_d Typical delay time	1.0	μs	Gate current A, $di_g/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ C$
t_q Typical turn-off time	100		$I_{TM} = 550A$, $T_J = T_{J\max}$, $di/dt = 40A/\mu s$, $V_R = 50V$ $dv/dt = 20V/\mu s$, Gate 0V 100Ω, $t_p = 500\mu s$

Blocking

Parameter	ST330S	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = T_{J\max}$ linear to 80% rated V_{DRM}
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	50	mA	$T_J = T_{J\max}$, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter	ST330S	Units	Conditions
P_{GM} Maximum peak gate power	10.0	W	$T_J = T_{J\max}$, $t_p \leq 5ms$
$P_{G(AV)}$ Maximum average gate power	2.0		$T_J = T_{J\max}$, $f = 50Hz$, $d\% = 50$
I_{GM} Max. peak positive gate current	3.0	A	$T_J = T_{J\max}$, $t_p \leq 5ms$
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_{J\max}$, $t_p \leq 5ms$
$-V_{GM}$ Maximum peak negative gate voltage	5.0		
I_{GT} DC gate current required to trigger	TYP.	MAX.	Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
	200	-	
	100	200	
	50	-	
V_{GT} DC gate voltage required to trigger	2.5	-	$T_J = -40^\circ C$
	1.8	3.0	$T_J = 25^\circ C$
	1.1	-	$T_J = 125^\circ C$
I_{GD} DC gate current not to trigger	10	mA	Max. gate current/ voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied
V_{GD} DC gate voltage not to trigger	0.25	V	

ST330S Series

Thermal and Mechanical Specification

Parameter	ST330S	Units	Conditions
T_J	Max. operating temperature range	-40 to 125	°C
T_{stg}	Max. storage temperature range	-40 to 150	
R_{thJC}	Max. thermal resistance, junction to case	0.10	K/W
R_{thCS}	Max. thermal resistance, case to heatsink	0.03	
T	Mounting torque, $\pm 10\%$	48.5 (425)	Nm (lbf-in) Non lubricated threads
wt	Approximate weight	535	g
Case style	TO - 209AE (TO-118)	See Outline Table	

ΔR_{thJC} Conduction

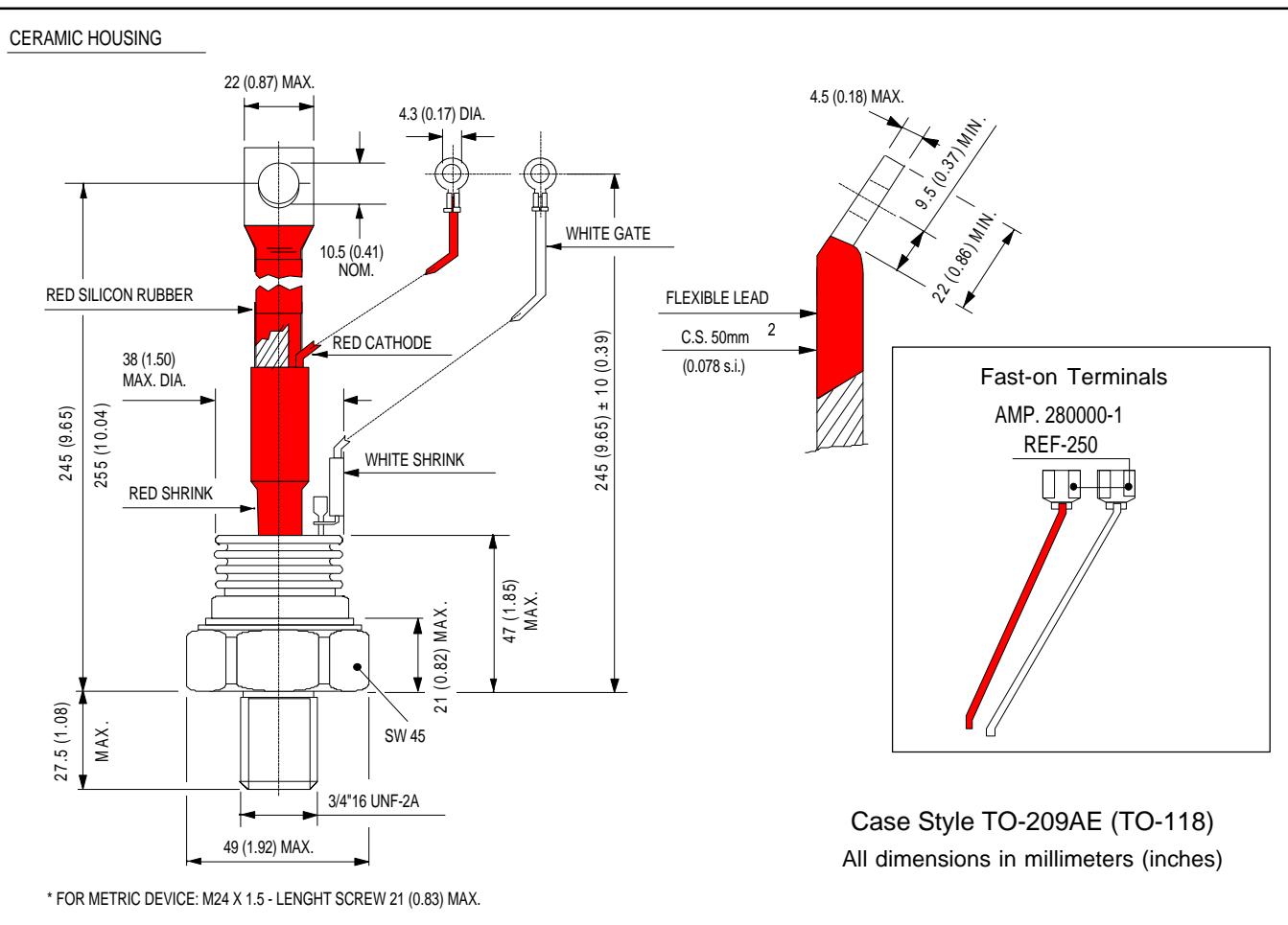
(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.011	0.008	K/W	$T_J = T_J$ max.
120°	0.013	0.014		
90°	0.017	0.018		
60°	0.025	0.026		
30°	0.041	0.041		

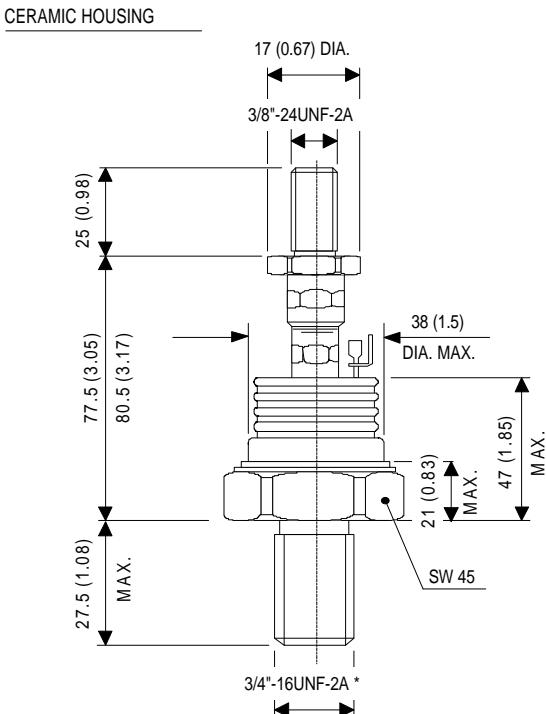
Ordering Information Table

Device Code	ST	33	0	S	16	P	0	
	1	2	3	4	5	6	7	8
1	- Thyristor							
2	- Essential part number							
3	- 0 = Converter grade							
4	- S = Compression bonding Stud							
5	- Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)							
6	- P = Stud base 16UNF threads							
	M = Stud base metric threads (M24 x 1.5)							
7	- 0 = Eyelet terminals (Gate and Auxiliary Cathode Leads)							
	1 = Fast - on terminals (Gate and Auxiliary Cathode Leads)							
	3 = Threaded top terminal 3/8" 24UNF-2A							
8	- Critical dv/dt: None = 500V/ μ sec (Standard selection)							
	L = 1000V/ μ sec (Special selection)							

Outline Table



Case Style TO-209AE (TO-118)
with top thread terminal 3/8"
All dimensions in millimeters (inches)



* FOR METRIC DEVICE: M24 x 1.5 - LENGTH SCREW 21 (0.83) MAX.